

## Deployment in Chemical Vapor Deposition Applications<sup>1</sup>

Table 1: Chemical Vapor Deposition Target

| Target Type                  | MFL (Ours) | Ideal Target |
|------------------------------|------------|--------------|
| Film thickness (center) [nm] | 1047.5     | (100, 2000)  |
| Film thickness (edge) [nm]   | 1147.3     | (100, 2200)  |
| Internal stress [MPa]        | 0.0        | 0.047        |
| Surface roughness (Ra) [nm]  | 5.148      | (0.1, 10)    |

Table 2: Chemical Vapor Deposition Input

| Input Type                        | MFL (Ours) | Input Constraints |
|-----------------------------------|------------|-------------------|
| SiH <sub>4</sub> flow rate [sccm] | 317.0320   | (50, 500)         |
| NH <sub>3</sub> flow rate [sccm]  | 560.5539   | (100, 1000)       |
| N <sub>2</sub> flow rate [sccm]   | 1288.5685  | (200, 2000)       |
| Chamber temperature [°C]          | 541.5430   | (300, 750)        |
| Chamber pressure [Torr]           | 5.1651     | (1, 10)           |
| Chamber humidity [%RH]            | 24.6166    | (5, 40)           |
| Electrode distance [mm]           | 16.7863    | (10, 30)          |
| Pre-clean plasma power [W]        | 146.6214   | (0, 300)          |
| Pre-clean duration [s]            | 36.2421    | (0, 60)           |
| Wafer rotation speed [rpm]        | 1906.4441  | (0, 3000)         |
| Process time [s]                  | 5.05       | 144.5516          |

## Deployment in Wire Bonding Applications<sup>2</sup>

Table 3: Wire Bonding Target

| Target Type           | MFL (Ours) | Ideal Target |
|-----------------------|------------|--------------|
| Pull strength [gf]    | 15.005     | (5, 25)      |
| Bonding x-offset [μm] | -0.0001    | (-20, 20)    |
| Bonding y-offset [μm] | -0.0002    | (-20, 20)    |

Table 4: Table 4: Wire Bonding Input

| Input Type            | MFL (Ours) | Input Constraints |
|-----------------------|------------|-------------------|
| Bonding pressure [gf] | 98.6096    | (20, 120)         |
| Bonding time [ms]     | 19.9200    | (1, 30)           |
| Temperature [°C]      | 240.9897   | (100, 300)        |
| Wire diameter [μm]    | 28.0635    | (15, 33)          |
| Wire length [mm]      | 3.2536     | (0.5, 5.0)        |
| Pad diameter [μm]     | 88.7107    | (50, 150)         |

The applications in chemical vapor deposition and wire bonding are beyond the semiconductor recipe generation, these results highlight the generality and adaptability of our method across diverse tasks in different domains. We believe this extension demonstrates the broader applicability of our method.

## Ablation Experiments

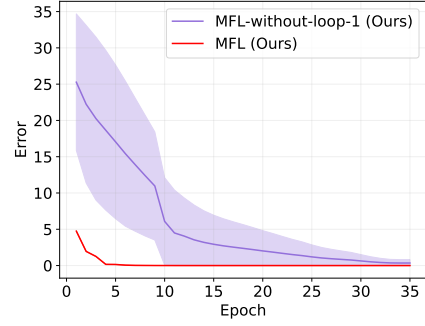


Figure 1: Ablation experiments: comparison between MFL and MFL without loop 1 training.

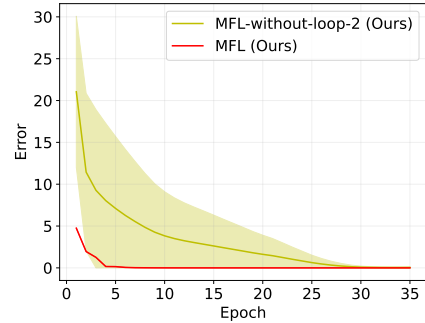


Figure 2: Ablation experiments: comparison between MFL and MFL without loop 2 training.

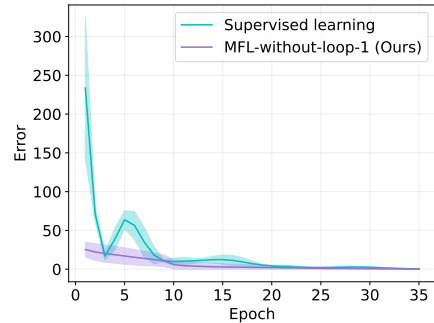


Figure 3: Ablation experiments: comparison between MFL without loop 1 training and supervised learning.

<sup>1</sup>[https://en.wikipedia.org/wiki/Chemical\\_vapor\\_deposition](https://en.wikipedia.org/wiki/Chemical_vapor_deposition)

<sup>2</sup>[https://en.wikipedia.org/wiki/Wire\\_bonding](https://en.wikipedia.org/wiki/Wire_bonding)